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(54) SEMICONDUCTOR PACKAGE AND METHOD FOR MANUFACTURING THE

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ABSTRACT (57)

A semiconductor package and a manufacturing method thereof are disclosed. The semiconductor package and manufacturing method thereof according to an aspect of the present invention may include an antenna structure including a dielectric layer made of a transparent material, an active antenna pattern formed on one surface of the dielectric layer and a parasitic antenna pattern formed on the other surface of the dielectric layer opposite to the one surface; a first rewiring structure electrically connected to the active antenna pattern of the antenna structure; a molding body formed on one surface of the first rewiring structure; a semiconductor chip placed within the molding body; a second rewiring structure formed on one surface of the molding body; a vertical connection conductor laterally spaced from the semiconductor chip, penetrating the molding layer, and electrically connecting the second rewiring structure and the first rewiring structure; and an external connection terminal formed on one surface of the second rewiring structure.

